●Application

General rectification

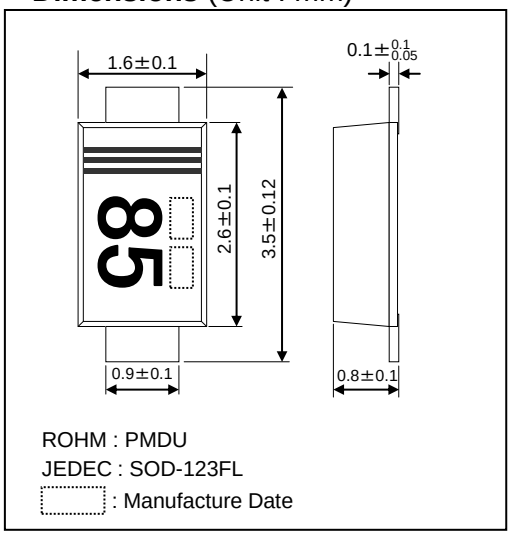
●Features

1) Small power mold type (PMDU)
2) High reliability
3) Low V_F

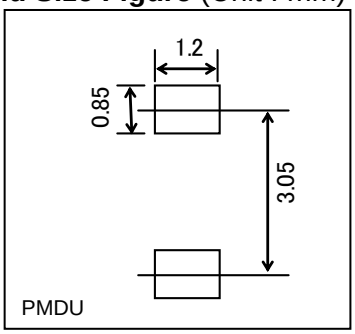
●Construction

Silicon epitaxial planar type

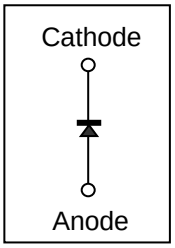
●Dimensions (Unit : mm)



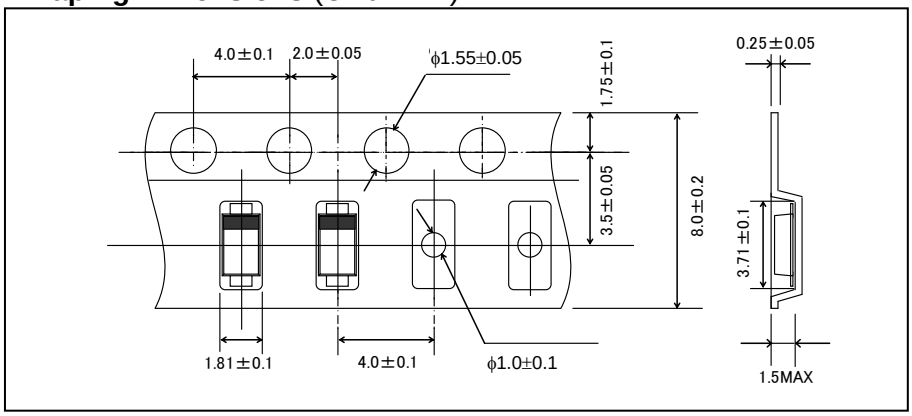
●Land Size Figure (Unit : mm)



●Structure



●Taping Dimensions (Unit : mm)



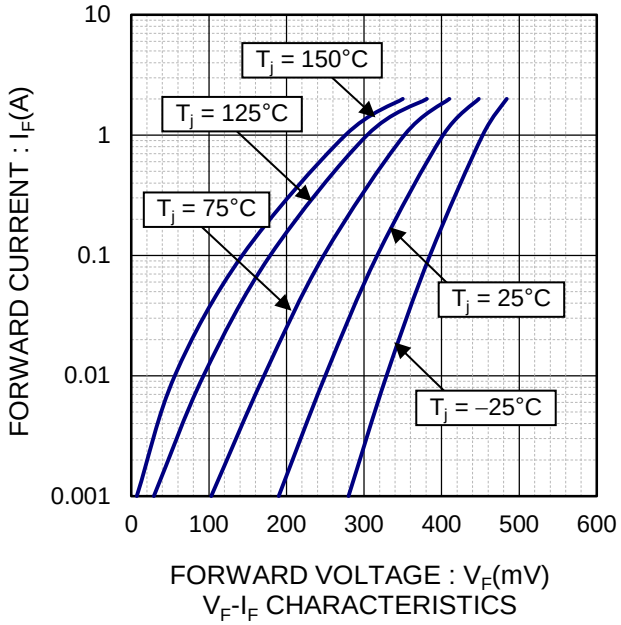
●Absolute Maximum Ratings (T_c= 25°C)

Parameter	Symbol	Conditions	Limits	Unit
Repetitive Peak Reverse Voltage	V_{RM}	Duty≦0.5	30	V
Reverse Voltage	V_R	Direct Reverse Voltage	30	V
Average Forward Rectified Current	I_o	Glass epoxi mounted, 60Hz half sin Wave resistive load, T_c=65°C max.	2	A
Non-repetitive Forward Current Surge Peak	I_{FSM}	60Hz half sin wave ,Non-repetitive at T_a=25°C	55	A
Operating Junction Temperature	T_j	-	150	°C
Storage Temperature	T_{stg}	-	−55 to +150	°C

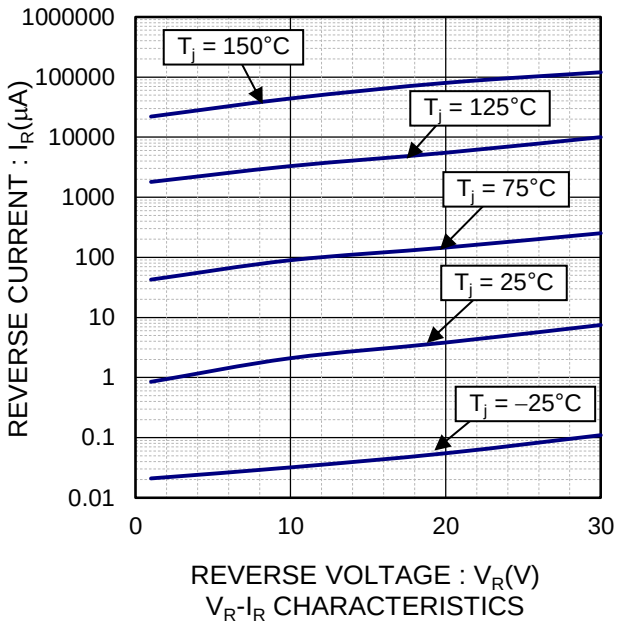
●Electrical Characteristics (T_j = 25°C)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward Voltage	V_{F1}	I_F=1.0A	0.32	0.40	0.45	V
	V_{F2}	I_F=2.0A	0.36	0.44	0.49	V
Reverse Current	I_R	V_R=30V	-	10	50	μA

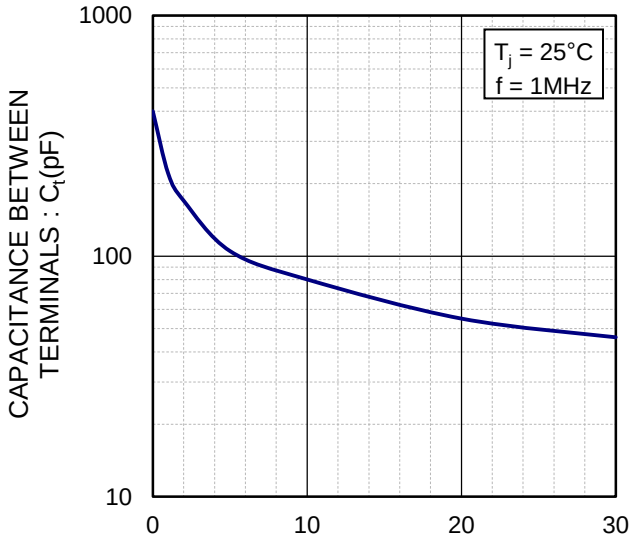
●Electrical Characteristic Curves



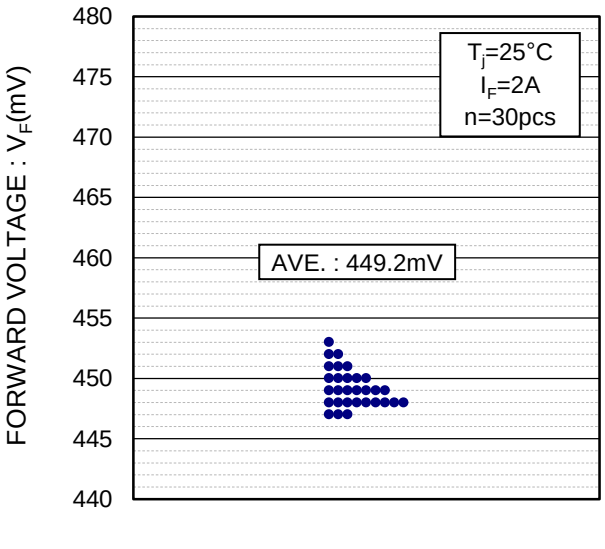
V_F-I_F CHARACTERISTICS



V_R-I_R CHARACTERISTICS

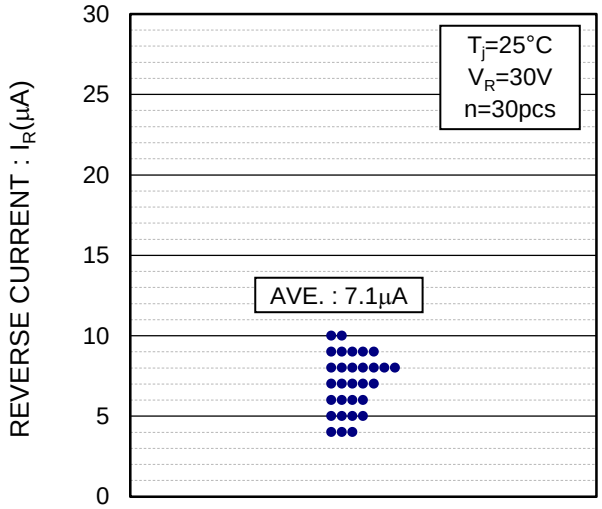


V_R-C_t CHARACTERISTICS

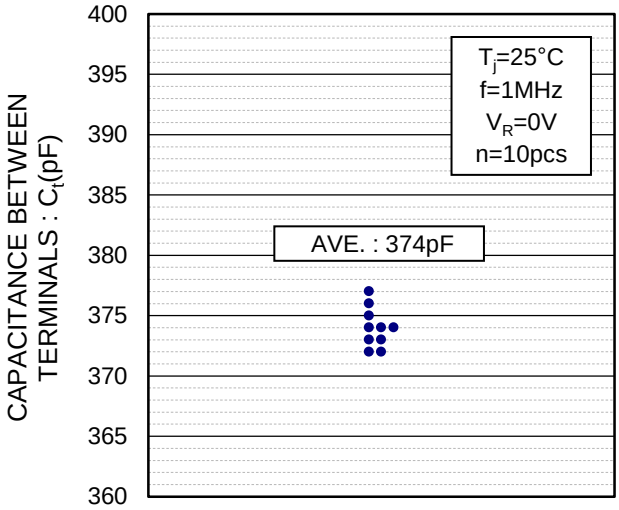


V_F DISPERSION MAP

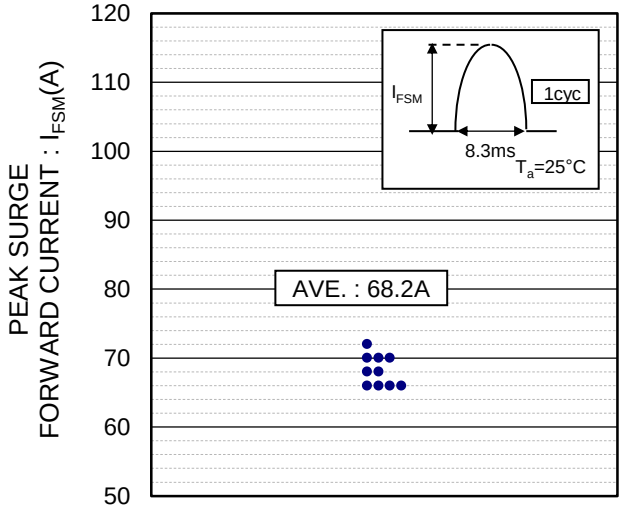
●Electrical Characteristic Curves



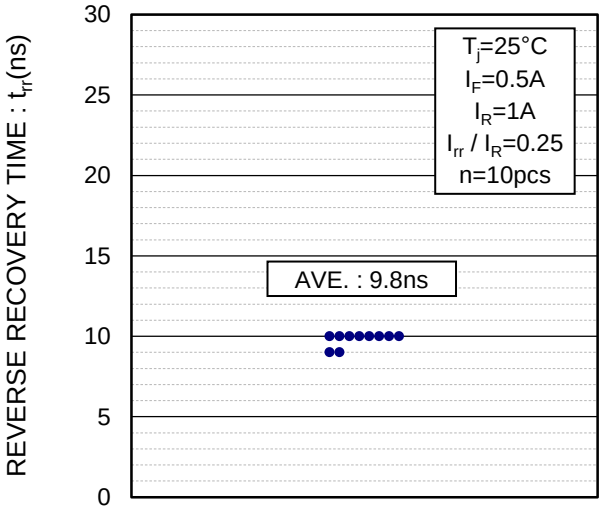
I_R DISPERSION MAP



C_t DISPERSION MAP

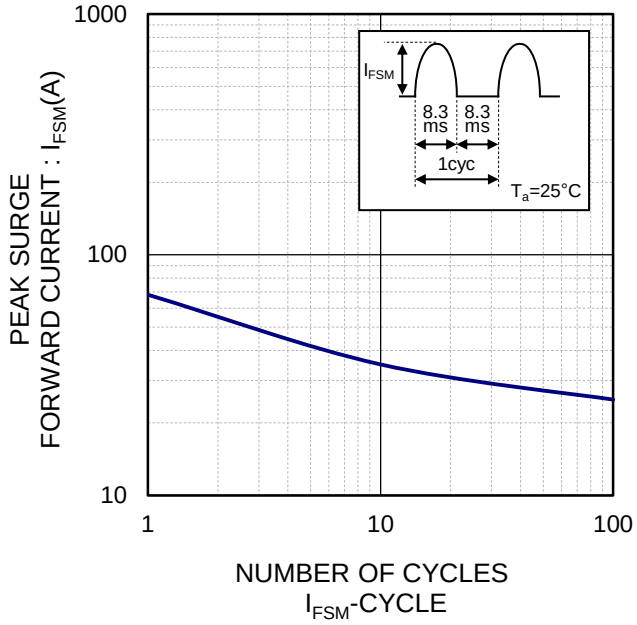


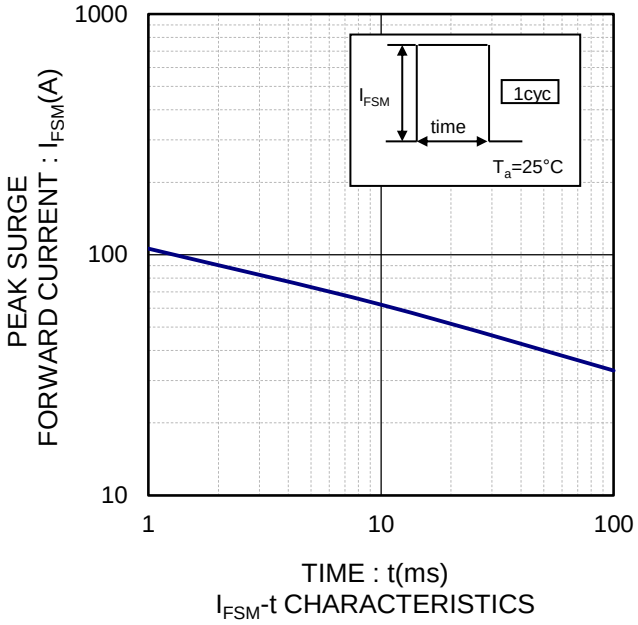
I_{FSM} DISPERSION MAP

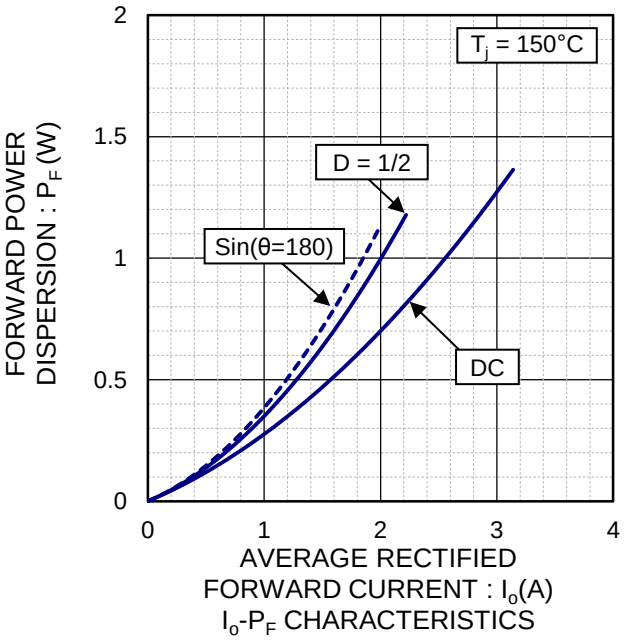


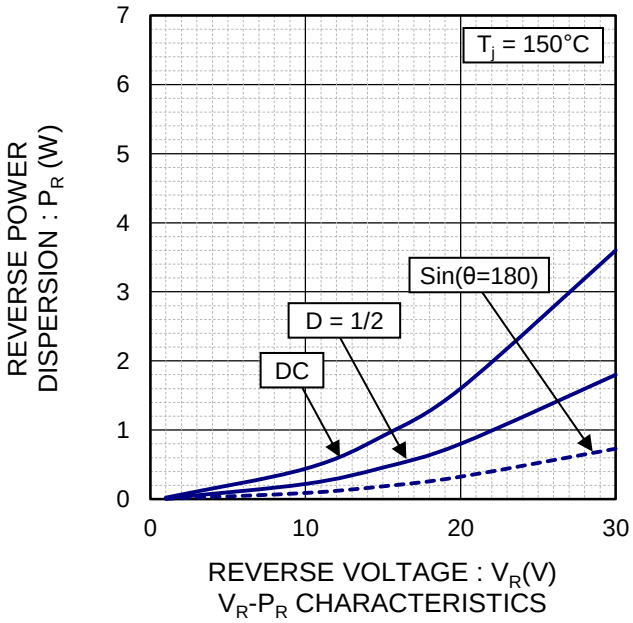
t_{rr} DISPERSION MAP

●Electrical Characteristic Curves

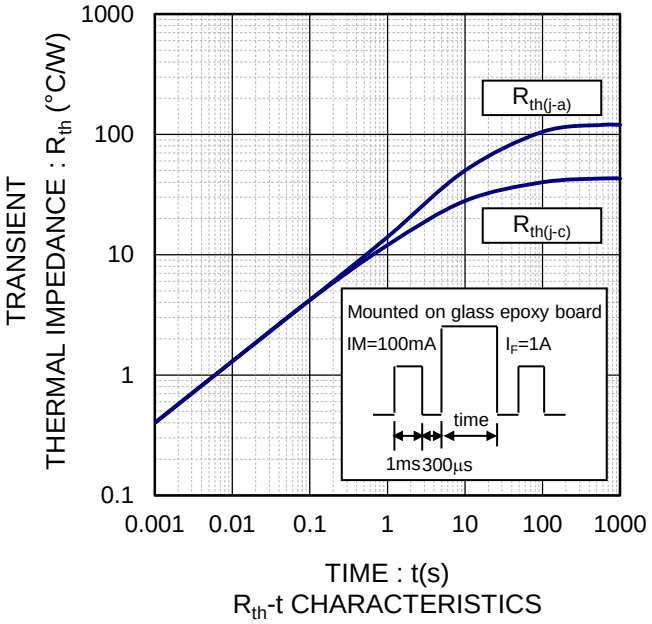




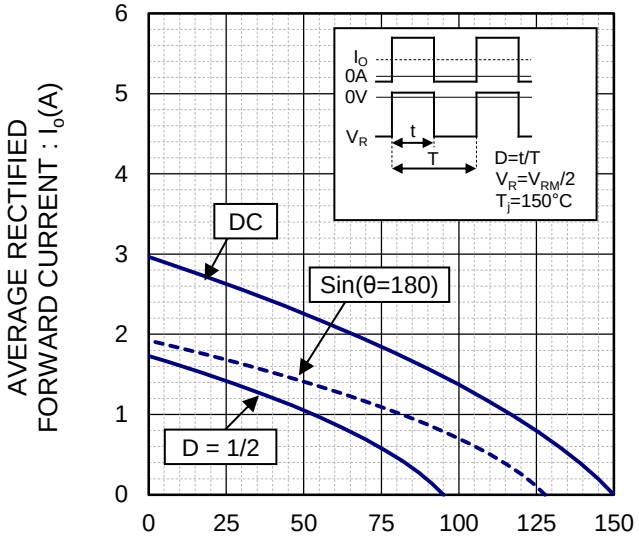




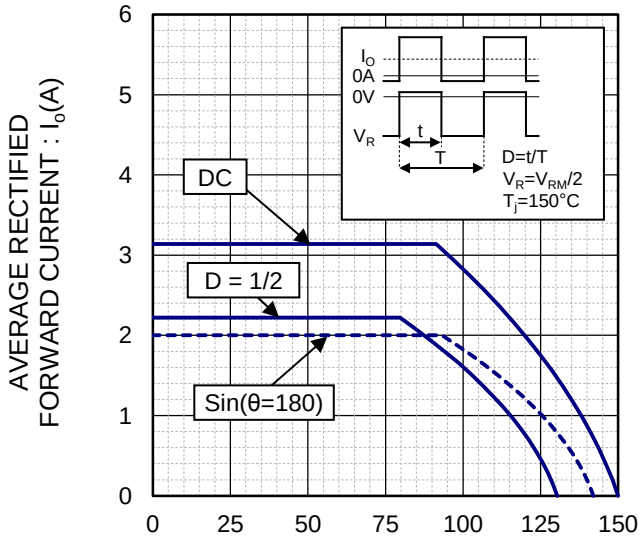
●Electrical Characteristic Curves



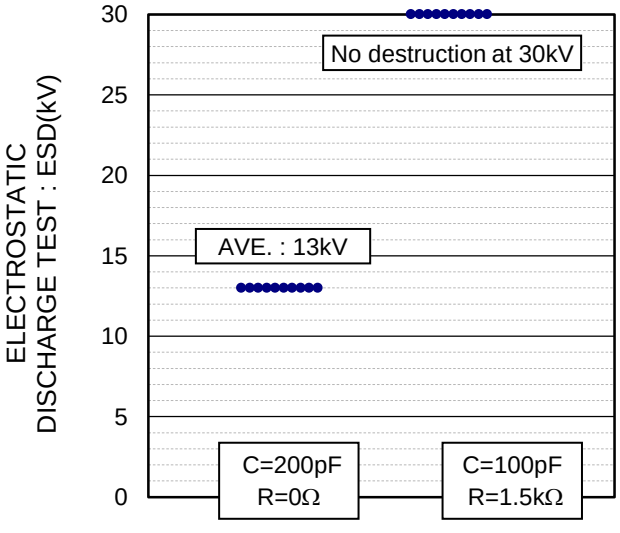
R_{th}-t CHARACTERISTICS



DERATING CURVE (I_o-T_a)



DERATING CURVE (I_o-T_c)



ESD DISPERSION MAP